

Dual Channel Small Outline Optoisolators Transistor Output

The MOCD211 device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline, plastic package. It is ideally suited for high density applications and eliminates the need for through-the-board mounting.

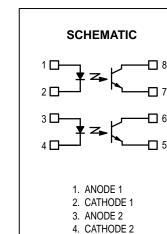
- Dual Channel Coupler
- Convenient Plastic SOIC-8 Surface Mountable Package Style
- Minimum V(BR)CEO of 30 Volts Guaranteed
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- · Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input–Output Isolation of 3000 Vac (rms) Guaranteed
- Meets U.L. Regulatory Requirements, File #E90700, Volume 2

Ordering Information:

- To obtain MOCD211 in tape and reel, add R2 suffix to device number as follows: R2 = 2500 units on 13" reel
- To obtain MOCD211 in quantities of 50 (shipped in sleeves) no suffix

Marking Information:

• MOCD211 = D211



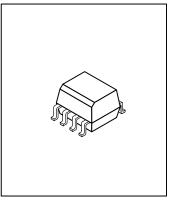
- 5. EMITTER 2
- 6. COLLECTOR 2
- 7. EMITTER 1
- 8. COLLECTOR 1

MAXIMUM	RATINGS	$(T_{\Delta} = 25^{\circ}C \text{ unless otherwise noted})$
	117111100	$(12 - 20 \ 0 \ 0 \ 0 \ 0 \ 0 \ 0 \ 0 \ 0 \ 0 $

Rating	Symbol	Value	Unit					
INPUT LED								
Forward Current — Continuous	١F	60	mA					
Forward Current — Peak (PW = 100 µs, 120 pps)	I _F (pk)	1.0	А					
Reverse Voltage	VR	6.0	V					
LED Power Dissipation @ T _A = 25°C Derate above 25°C	PD	90 0.8	mW mW/°C					
OUTPUT TRANSISTOR								
Collector–Emitter Voltage	VCEO	30	V					
Collector–Base Voltage	VCBO	70	V					
Emitter–Collector Voltage	VECO	7.0	V					
Collector Current — Continuous	ΙC	150	mA					
Detector Power Dissipation @ T _A = 25°C Derate above 25°C	PD	150 1.76	mW mW/°C					



DUAL CHANNEL SMALL OUTLINE OPTOISOLATOR TRANSISTOR OUTPUT





MAXIMUM RATINGS — continued (T_A = 25°C unless otherwise noted)

F		Symbol	nbol Value		Unit	
TOTAL DEVICE						
Input–Output Isolation Voltage ^(1,2) (60 Hz, 1.0 sec. duration)		VISO 3000			Vac(rms)	
Total Device Power Dissipation @ T Derate above 25°C		PD	250 2.94		mW mW/°C	
Ambient Operating Temperature Rat		TA	T _A -45 to +100		°C	
Storage Temperature Range ⁽³⁾		T _{stg}	-45 to +125		°C	
Lead Soldering Temperature (1/16" from case, 10 sec. duration		_	260		°C	
ELECTRICAL CHARACTERISTI	CS ($T_A = 25^{\circ}C$ unless otherwise	e noted)(4)				
Characteristic		Symbol	Min	Typ (4)	Max	Unit
INPUT LED			•	1		
Forward Voltage (I _F = 1.0 mA)		VF	—	1.15	1.5	V
Reverse Leakage Current (V _R = 6.0 V)		IR		0.1	100	μΑ
Capacitance		С		18	_	pF
OUTPUT TRANSISTOR			•	1		
Collector–Emitter Dark Current	$(V_{CE} = 5.0 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C})$	ICEO1	-	1.0	50	nA
	$(V_{CE} = 5.0 \text{ V}, \text{ T}_{A} = 100^{\circ}\text{C})$	ICEO2	—	1.0	_	μA
Collector–Emitter Breakdown Voltage (IC = 100 µA)		V(BR)CEC) 30	90	_	V
Emitter–Collector Breakdown Voltag	V(BR)ECO	, 7.0	7.8		V	
Collector-Emitter Capacitance (f = 1	CCE		7.0		pF	
COUPLED			•	1		
Output Collector Current ($I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}$)	MOCD211	I _C (CTR) ⁽⁵) 2.0 (20)	6.5 (65)	—	mA (%)
Collector–Emitter Saturation Voltage ($I_C = 2.0 \text{ mA}, I_F = 1.0 \text{ mA}$)		VCE(sat)	_	0.15	0.4	V
Turn–On Time (I _C = 2.0 mA, V _{CC} = 10 V, R _L = 100 Ω)		ton		7.5	_	μs
Turn–Off Time (I _C = 2.0 mA, V _{CC} = 10 V, R _L = 100 Ω)		toff		5.7		μs
Rise Time (I _C = 2.0 mA, V _{CC} = 10 V, R _L = 100 Ω)		tr		3.2		μs
Fall Time (I _C = 2.0 mA, V _{CC} = 10 V, R _L = 100 Ω)		tf		4.7	_	μs
Input–Output Isolation Voltage (f = 60 Hz, t = 1.0 sec.) ^(1,2)		VISO	3000	_	_	Vac(rms)
Isolation Resistance (VI–O = 500 V)	RISO	10 ¹¹	_	_	Ω	
Isolation Capacitance ($V_{I-O} = 0$, f =	CISO		0.2		pF	

1. Input–Output Isolation Voltage, $V_{\mbox{\scriptsize ISO}},$ is an internal device dielectric breakdown rating.

2. For this test, pins 1, 2, 3 and 4 are common, and pins 5, 6, 7 and 8 are common.

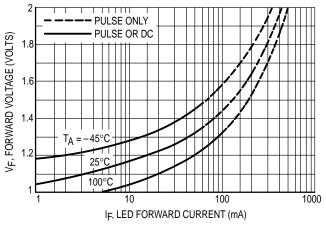
3. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

4. Always design to the specified minimum/maximum electrical limits (where applicable).

5. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.



MOCD211



TYPICAL CHARACTERISTICS





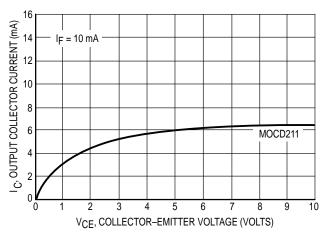


Figure 3. Output Current versus Collector–Emitter Voltage

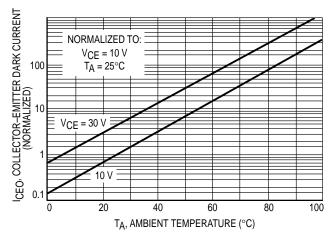


Figure 5. Dark Current versus Ambient Temperature

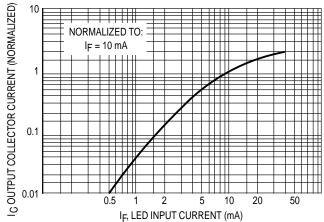


Figure 2. Output Current versus Input Current

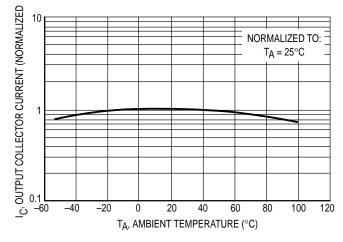


Figure 4. Output Current versus Ambient Temperature

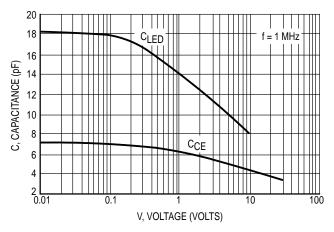
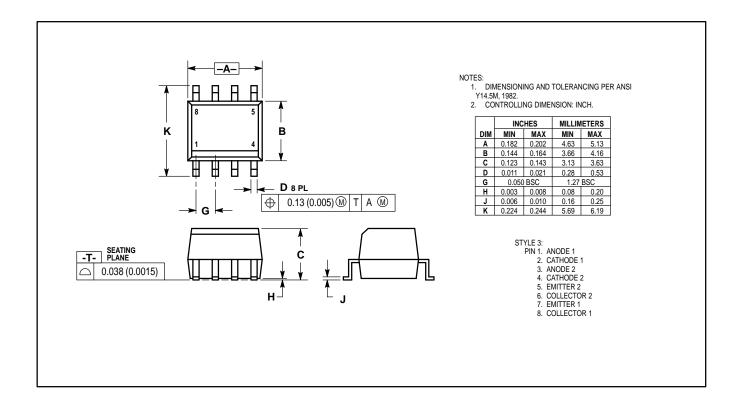


Figure 6. Capacitance versus Voltage







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